

PW502K

50V P-Channel MOSFET

-0.18A -50V; $R_{DS(ON)typ}=2.7\Omega@-5V$, $R_{DS(ON)typ}=2.3\Omega@-10V$.

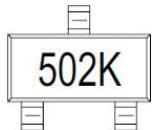
FEATURE

- Energy Efficient
- Low Threshold Voltage
- High-speed Switching
- Miniature Surface Mount Package Saves Board Space

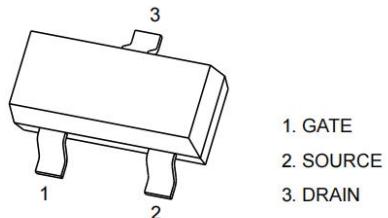
Application

DC-DC converters, load switching, power management in portable and battery-powered products such as computers, printers, cellular and cordless telephones.

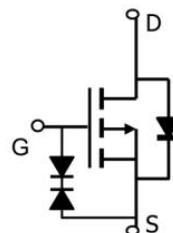
MARKING:



SOT-23



Schematic diagram



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ C$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	-50	V
Gate-Source Voltage	V_{GS}	± 20	V
Continuous Drain Current	I_D	-0.18	A
Plused Drain Current ⁽¹⁾ @ $t_p < 10\mu s$	I_{DM}	-0.54	A
Power Dissipation	P_D	225	mW
Thermal Resistance from Junction to Ambient ⁽²⁾	$R_{\theta JA}$	556	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C

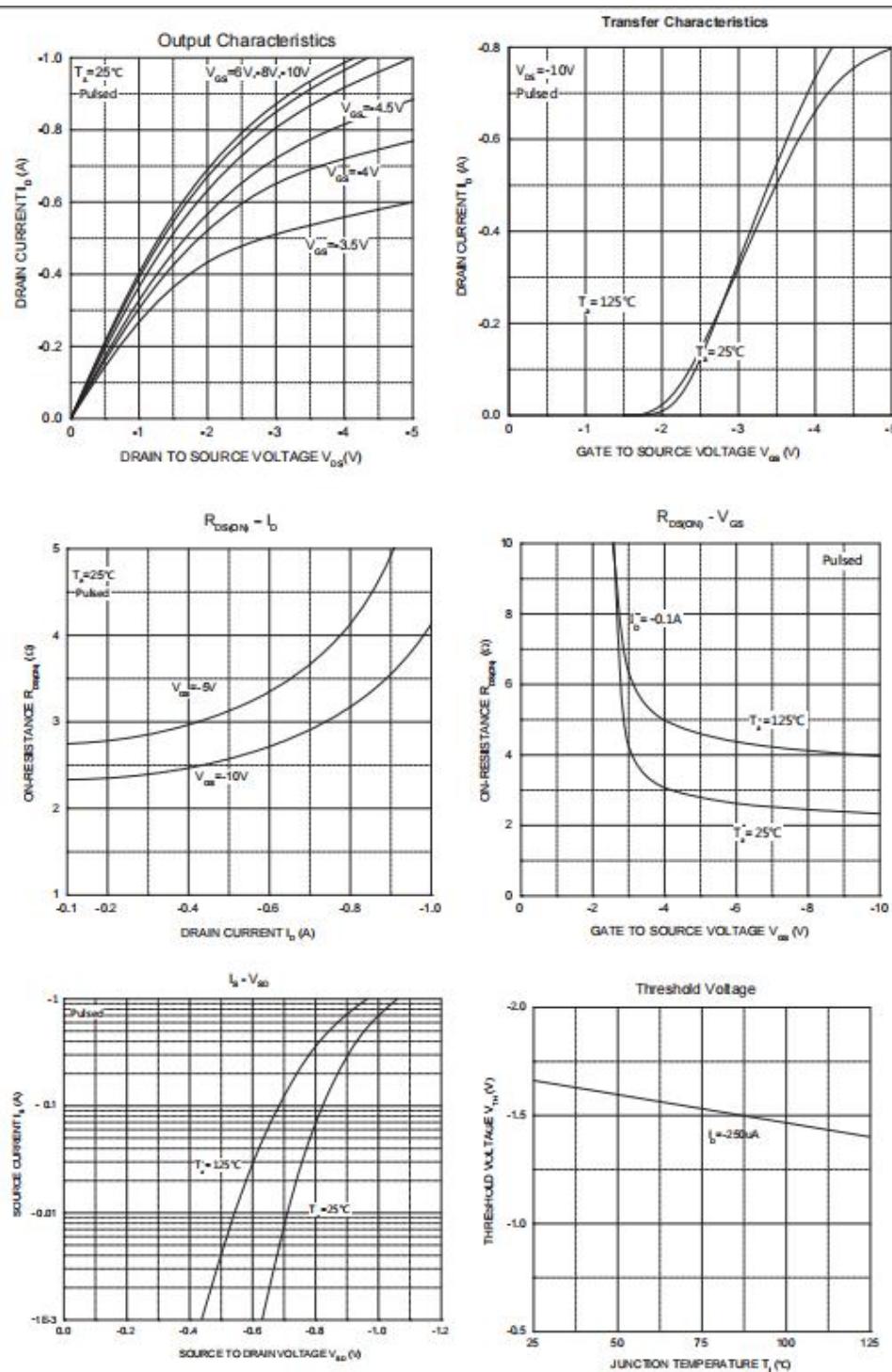
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
STATIC CHARACTERISTICS						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-50			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = -50\text{V}, V_{\text{GS}} = 0\text{V}$			-1	μA
		$V_{\text{DS}} = -25\text{V}, V_{\text{GS}} = 0\text{V}$			-0.1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 20\text{V}, V_{\text{DS}} = 0\text{V}$			± 5	uA
Gate threshold voltage ⁽³⁾	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = -250\mu\text{A}$	-0.9	-1.6	-2	V
Drain-source on-resistance ⁽³⁾	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = -10\text{V}, I_D = -0.1\text{A}$		2.3	6	Ω
		$V_{\text{GS}} = -5\text{V}, I_D = -0.1\text{A}$		2.7	7	
		$V_{\text{DS}} = -25\text{V}, I_D = -0.1\text{A}$	50			
Forward transconductance ⁽¹⁾	g_{FS}	$V_{\text{GS}} = 0\text{V}, I_D = -250\mu\text{A}$	-50			mS
DYNAMIC CHARACTERISTICS⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = -5\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		22		pF
Output Capacitance	C_{oss}			7.5		
Reverse Transfer Capacitance	C_{rss}			4		
SWITCHING CHARACTERISTICS⁽⁴⁾						
Turn-on delay time	$t_{\text{d}(\text{on})}$	$V_{\text{DD}} = -15\text{V}, R_L = 50\Omega, I_D = -2.5\text{A}$		1.85		nS
Turn-on rise time	t_r			0.7		
Turn-off delay time	$t_{\text{d}(\text{off})}$			12		
Turn-off fall time	t_f			6		
SOURCE-DRAIN DIODE CHARACTERISTICS						
Diode forward current	I_s				-0.13	A
Diode pulsed forward current	I_{SM}				-0.52	
Diode Forward voltage	V_{DS}	$V_{\text{GS}} = 0\text{V}, I_s = -0.13\text{A}$			-1.2	V

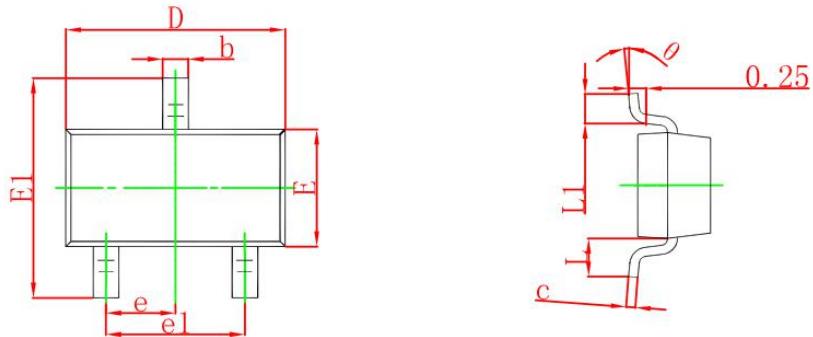
Notes :

- 1.Repetitive rating : Pulse width limited by junction temperature.
- 2.Surface mounted on FR4 board , $t \leqslant 10\text{s}$.
- 3.Pulse Test : Pulse Width $\leqslant 300\text{ }\mu\text{s}$, Duty Cycle $\leqslant 2\%$.
- 4.Guaranteed by design, not subject to producing.

Typical Electrical and Thermal Characteristics



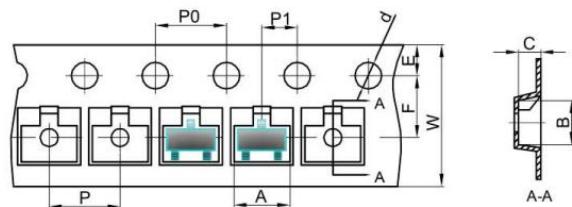
SOT-23 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

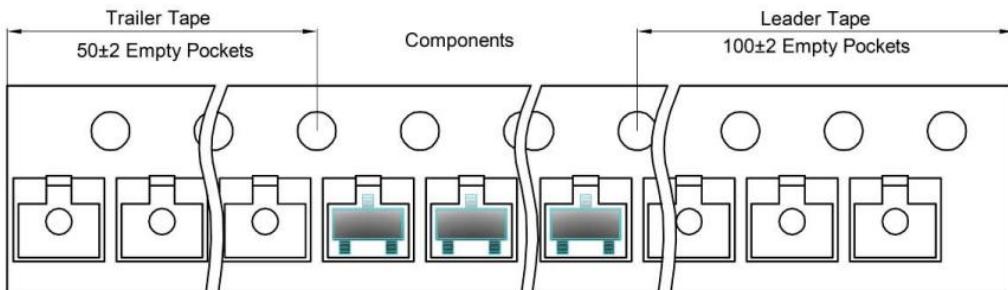
SOT-23 Tape and Reel

SOT-23 Embossed Carrier Tape

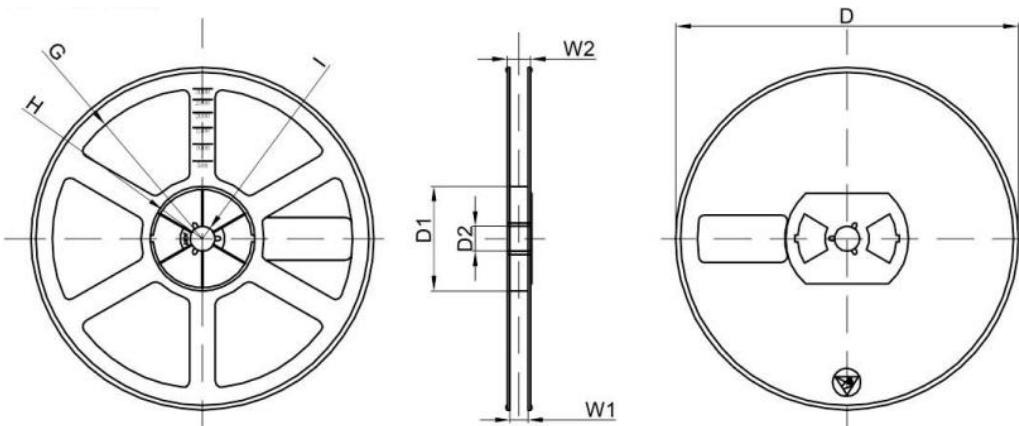


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-23	3.15	2.77	1.22	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-23 Tape Leader and Trailer



SOT-23 Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
3000 pcs	7 inch	30,000 pcs	203×203×195	120,000 pcs	438×438×220	